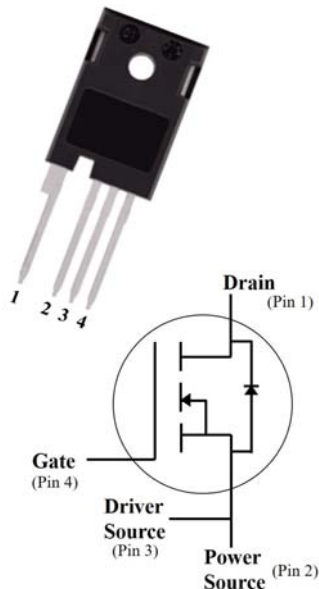


Silicon Carbide Power MOSFET (N-Channel Enhancement)

V_{DS}	1200V
I_D (25°C)	67A
$R_{DS(on)}$	34mΩ



Features

- High speed switching
- Essentially no switching losses
- Reduction of heat sink requirements
- Maximum working temperature at 175 °C
- High blocking voltage
- Fast Intrinsic diode with low recovery current
- High-frequency operation
- Halogen free, RoHS compliant

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- **Package:** TO-247-4L
- **Terminals:** Tin plated leads
- **Polarity:** As marked

■Maximum Ratings ($T_c=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE	TEST CONDITIONS	NOTE
Device marking code			D212040NCFYG3		
Drain source voltage @ $T_j=25^\circ\text{C}$	$V_{DS,max}$	V	1200	$V_{GS}=0V$, $I_D=100\mu A$	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,max}$	V	-8/+22	Absolute maximum values (AC f > 1Hz, duty cycle < 1%)	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,op}$	V	-5/+18	Recommended operational values	
Continuous drain current @ $T_c=25^\circ\text{C}$	I_D	A	67	$V_{GS}=18V$, $T_c=25^\circ\text{C}$	Fig.17
Continuous drain current @ $T_c=100^\circ\text{C}$			46	$V_{GS}=18V$, $T_c=100^\circ\text{C}$	
Pulsed drain current	$I_{D(pulsed)}$	A	180	Pulse width t_p limited by $T_{j,max}$	Fig.22
Avalanche energy,Single pulse	E_{AS}	mJ	870	$V_{DD}=75V$, $L=30mH$	
Power Dissipation	P_{TOT}	W	333	$T_c=25^\circ\text{C}$, $T_j = 175^\circ\text{C}$	Fig.16
Power Dissipation			165	$T_c=100^\circ\text{C}$, $T_j = 175^\circ\text{C}$	
Operating junction and Storage temperature range	T_j, T_{stg}	$^\circ\text{C}$	-55 to +175		
Soldering temperature	T_L	$^\circ\text{C}$	260	1.6mm (0.063") from case for 10s	
Mounting torque	T_M	Nm	0.6	M3 screw Maximum of mounting process: 3	



YJD212040NCFYG3

■Static Electrical Characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Gate threshold voltage	$V_{GS(th)}$	V	2.0	3.0	4.0	$V_{DS}=V_{GS}$, $I_D=12mA$	Fig.4, 11
				2.2		$V_{DS}=V_{GS}$, $I_D=12mA$, $T_j=175^\circ C$	
Drain source breakdown voltage	$V_{(BR)DSS}$	V	1200			$V_{GS}=0V$, $I_D=100\mu A$	
Drain source leakage current	I_{DSS}	μA		10	100	$V_{DS}=1200V$, $V_{GS}=0V$	
Gate source leakage current	I_{GSS}	nA		10	100	$V_{GS}=18V$, $V_{DS}=0V$	
Current drain source on-state resistance	$R_{DS(on)}$	m Ω		40		$V_{GS}=15V$, $I_D=30A$	Fig.5, 6, 7
				34	42	$V_{GS}=18V$, $I_D=30A$	
				62		$V_{GS}=15V$, $I_D=30A$, $T_j=175^\circ C$	
				56		$V_{GS}=18V$, $I_D=30A$, $T_j=175^\circ C$	
Transconductance	g_f	S		19		$V_{DS}=20V$, $I_D=30A$	Fig.4
				18		$V_{DS}=20V$, $I_D=30A$, $T_j=175^\circ C$	

■Dynamic Electrical Characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Input capacitance	C_{iss}	pF		3362		$V_{DS}=1000V$, $V_{GS}=0V$, $T_j=25^\circ C$, $f=1MHz$, $V_{AC}=25mV$	Fig.13, 14
Output capacitance	C_{oss}			119			
Reverse capacitance	C_{rss}			5.4			
Coss stored energy	E_{oss}	μJ		85			Fig.15
Gate source charge	Q_{gs}	nC		31		$V_{DS}=1000V$, $V_{GS}=-5/+18V$, $I_D=30A$	Fig.12
Gate drain charge	Q_{gd}			58			
Gate charge	Q_g			117			
Internal gate resistance	R_g	Ω		1.6		$f=1MHz$	

■Switching Characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Turn on delay time	$t_{d(on)}$	ns		11		$V_{DD}=1000V$, $V_{GS}=-5/+18V$, $I_D=30A$, $R_g=2.4\Omega$, $L=100\mu H$	Fig.21
Rise time	t_r			17			
Turn off delay time	$t_{d(off)}$	ns		28			
Fall time	t_f			11			
Turn on switching energy	E_{on}	μJ		363		$V_{DD}=1000V$, $V_{GS}=-5/+18V$, $I_D=30A$, $R_g=2.4\Omega$, $L=100\mu H$	Fig.19, 20
Turn off switching energy	E_{off}			95			



YJD212040NCFYG3

■Body diode characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Diode forward voltage	V _{SD}	V		4.7		V _{GS} =-5V, I _{SD} =15A	Fig.8
				3		V _{GS} =0V, I _{SD} =15A, T _j =175°C	Fig.9
Continuous diode forward current	I _S	A		51		V _{GS} =-5V, T _c =25°C	
Reverse recovery time	t _{rr}	nS		17		V _R =1000V, V _{GS} =-5V, I _D =30A, di/dt=2000A/uS	
Reverse recovery charge	Q _{rr}	nC		178			
Peak reverse recovery current	I _{rrm}	A		16			

■Thermal Characteristics (T_a=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Typ.
Thermal resistance	R _{θJ-C}	°C/W	0.45

■Typical Characteristics

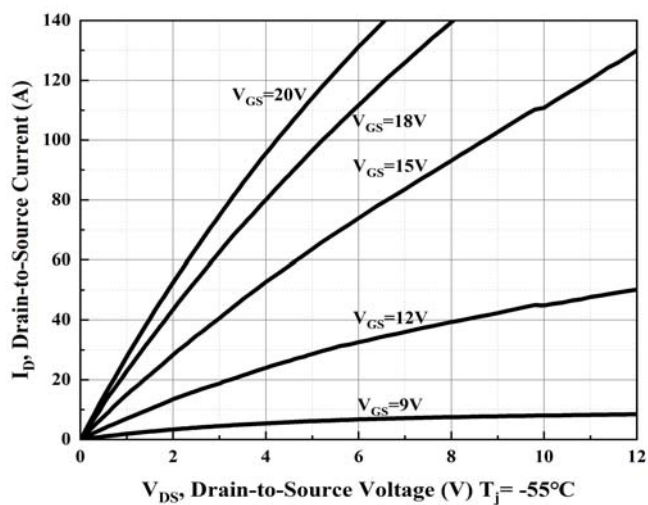


Figure 1. Output Characteristics T_j = -55°C

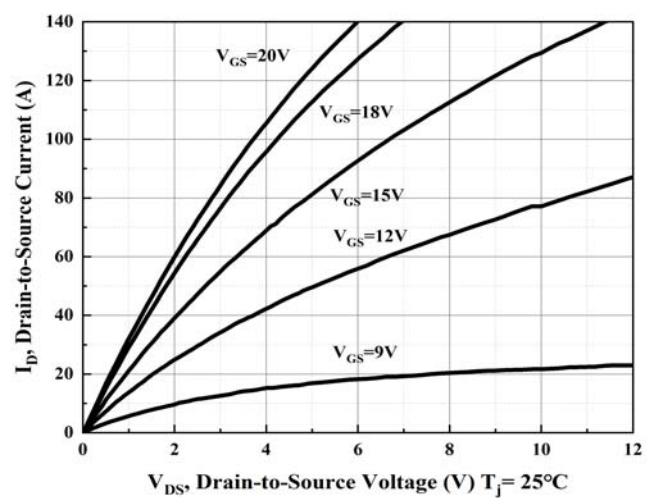


Figure2. Output Characteristics T_j = 25°C

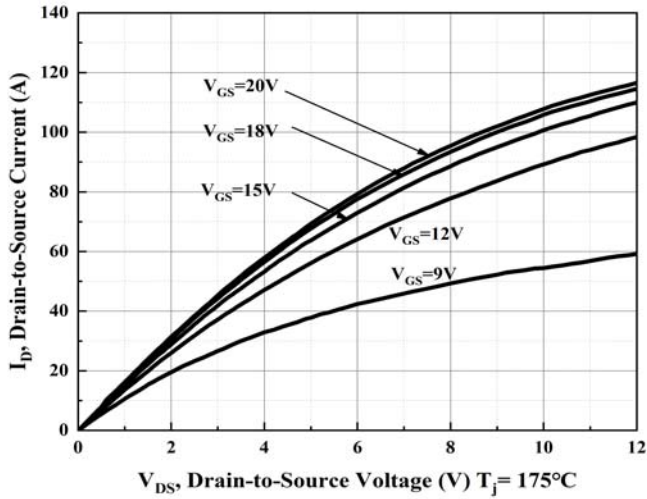


Figure 3. Output Characteristics $T_j = 175^\circ\text{C}$

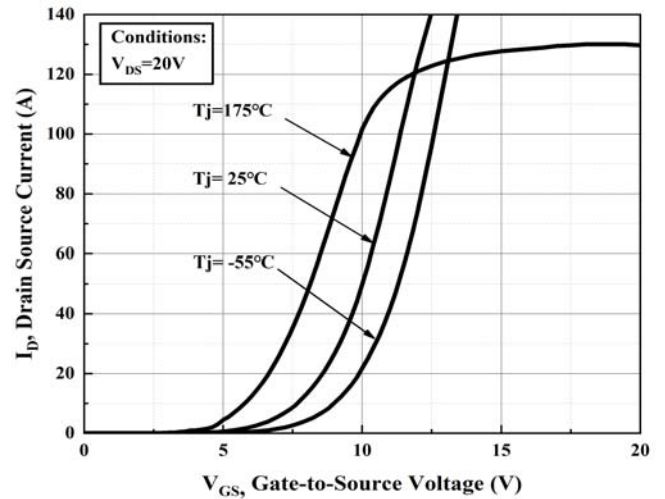


Figure 4. Transfer Characteristics for Various Junction Temperature

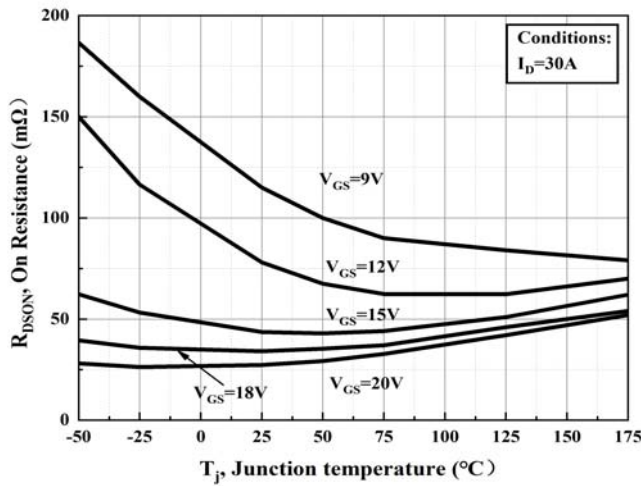


Figure 5. On-resistance vs. Temperature for Various Gate Voltage

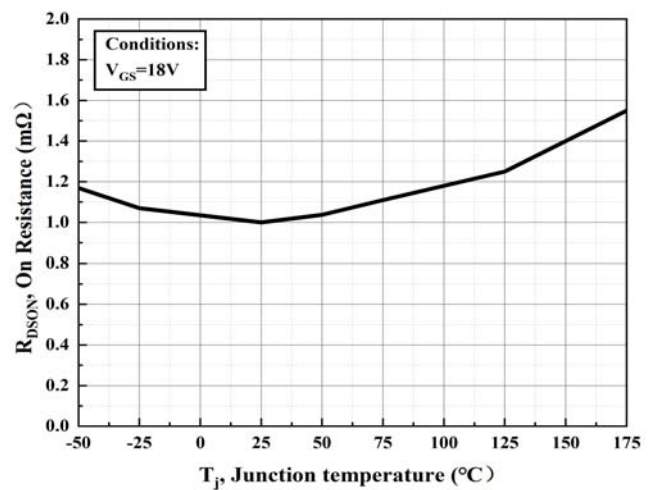


Figure 6. Normalized on-resistance vs. Temperature

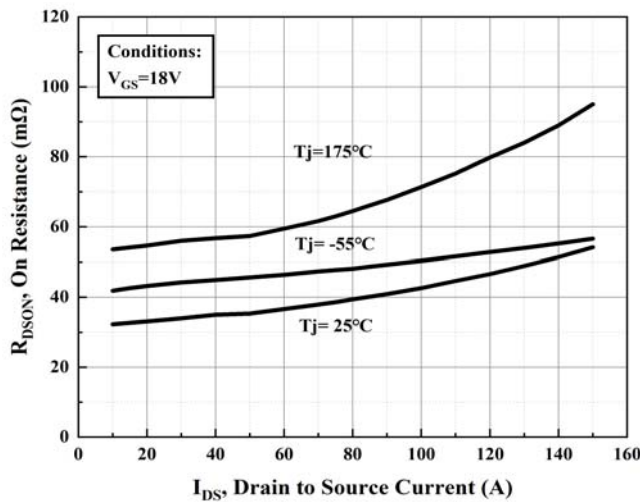


Figure 7. On-resistance vs. Drain Current

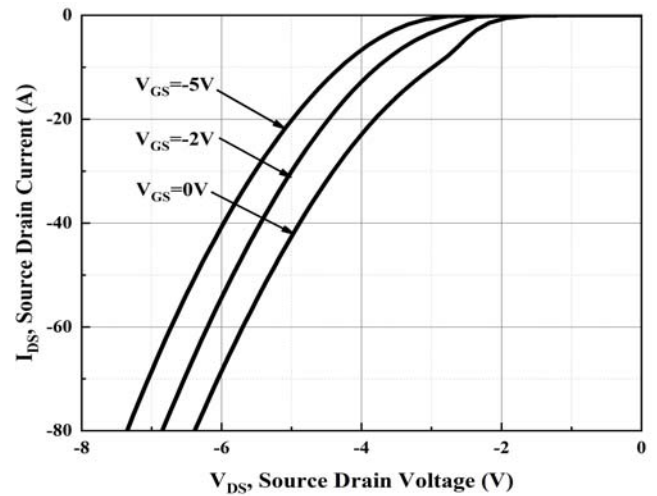


Figure 8. Body Diode Characteristic at $T_j = 25^\circ\text{C}$



YJD212040NCFYG3

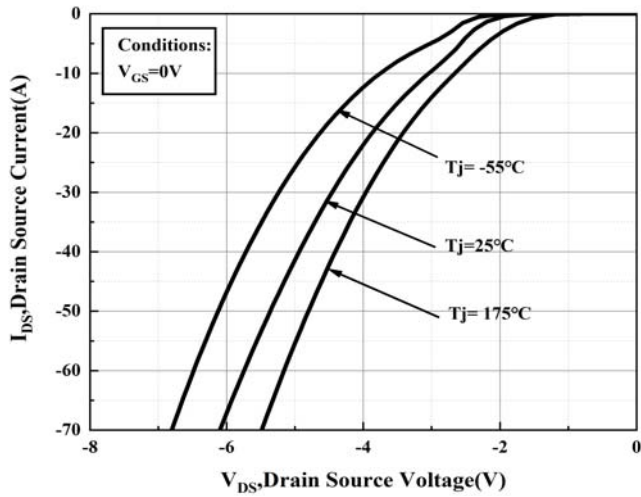


Figure 9. Body Diode Characteristic

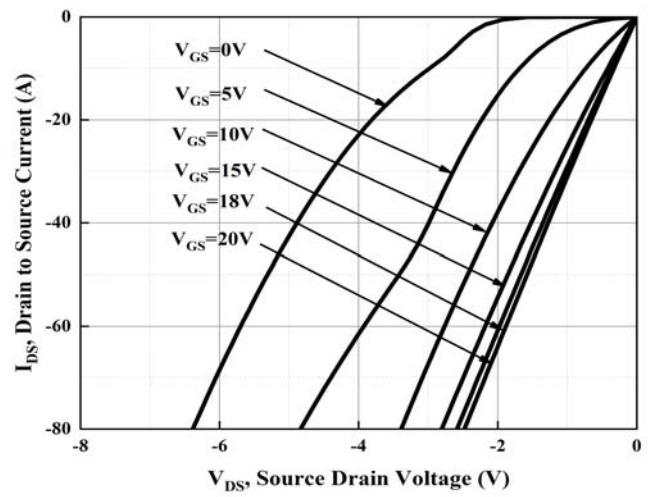


Figure 10. 3rd quadrant Characteristic at Tj= 25 °C

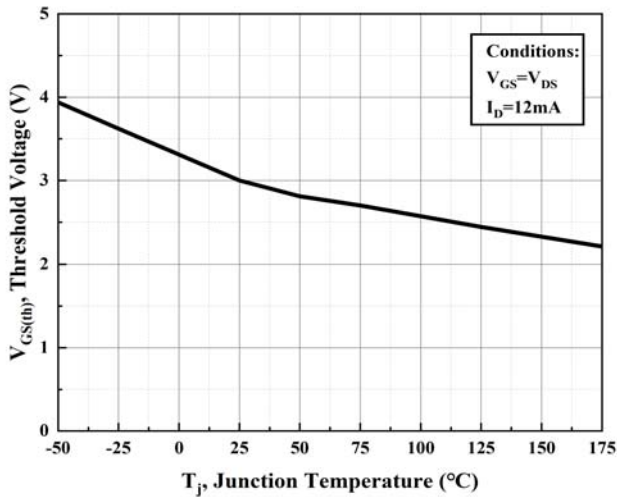


Figure 11. Threshold Voltage vs. Temperature

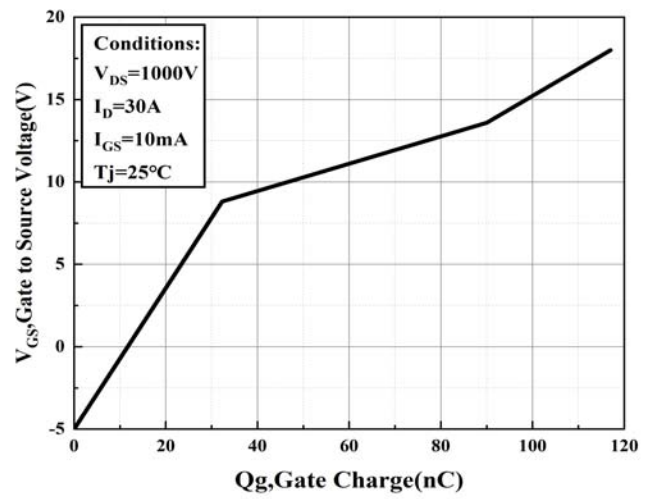


Figure 12. Gate Charge Characteristic

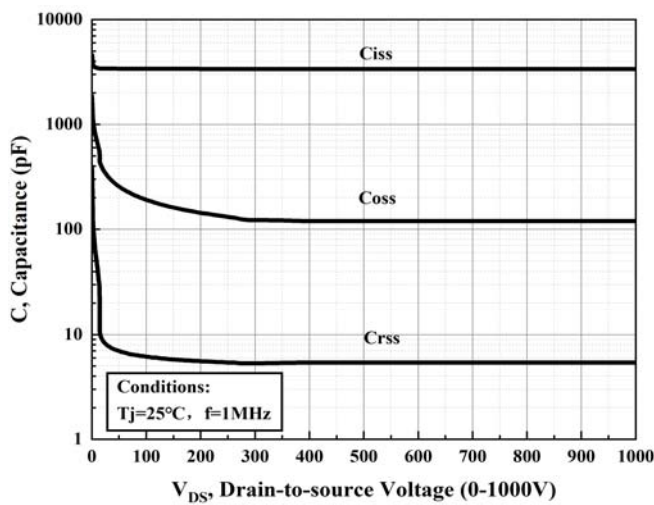


Figure 13. Capacitances vs. Drain Source Voltage (0-1000V)

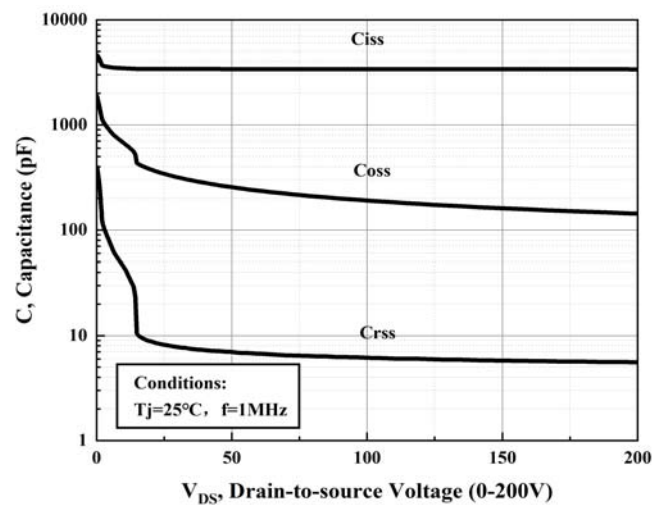


Figure 14. Capacitances vs. Drain Source Voltage (0-200V)

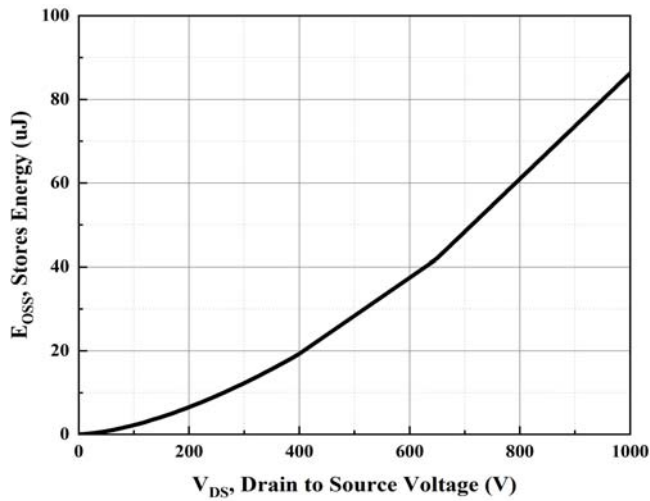


Figure 15. Output Capacitor Stored Energy

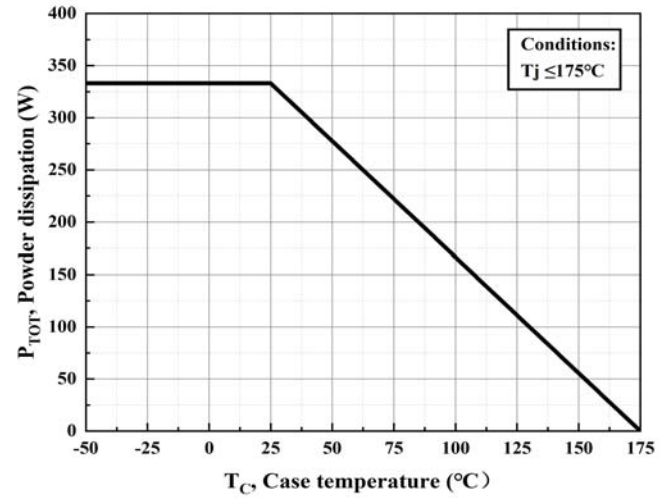


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

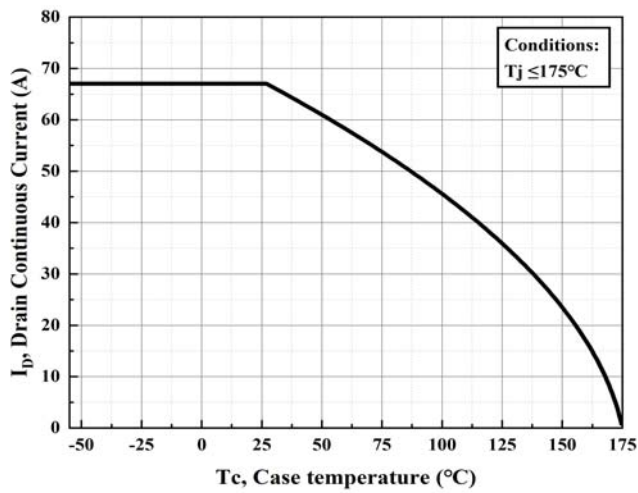


Figure 17. Continuous Drain Current Derating vs. Case Temperature

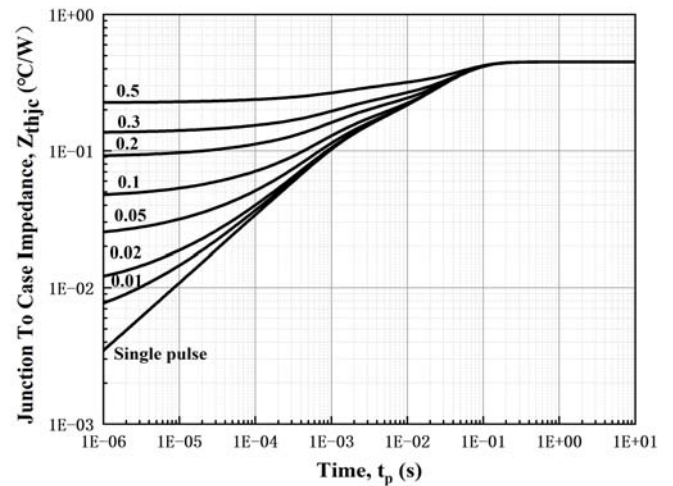


Figure 18 Transient Thermal Impedance (Junction - Case)

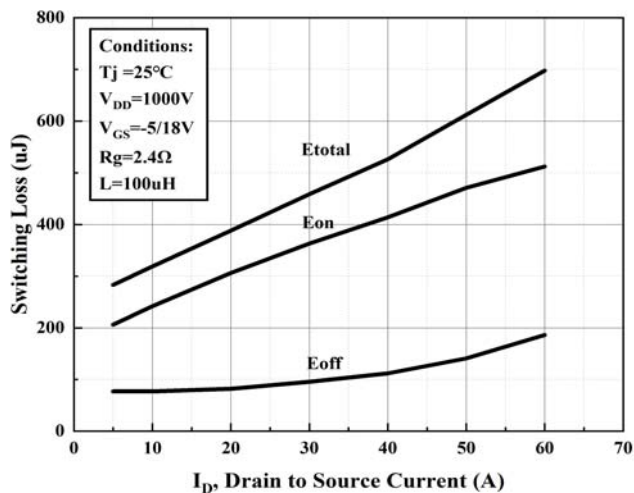


Figure 19. Clamped Inductive Switching Energy vs. Drain Current

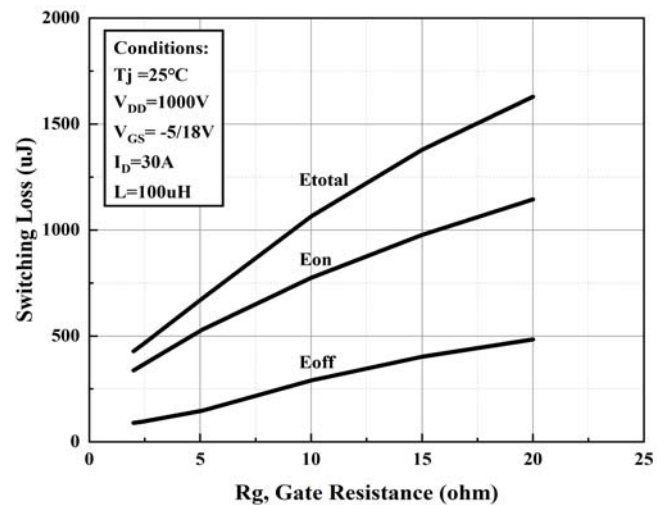


Figure 20. Clamped Inductive Switching Energy vs. Rg

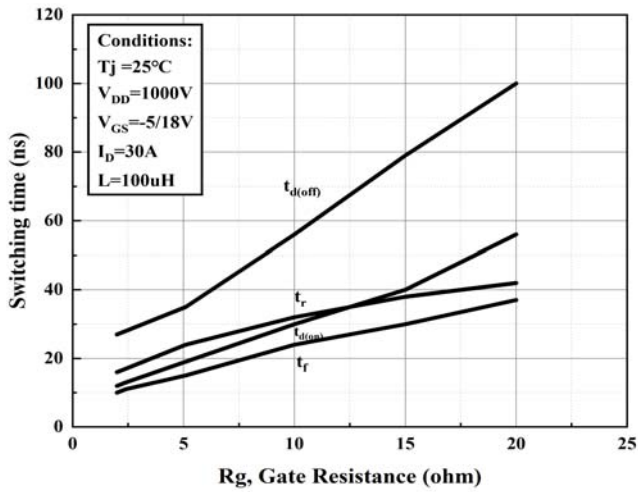


Figure 21. Switching Times vs. R_g

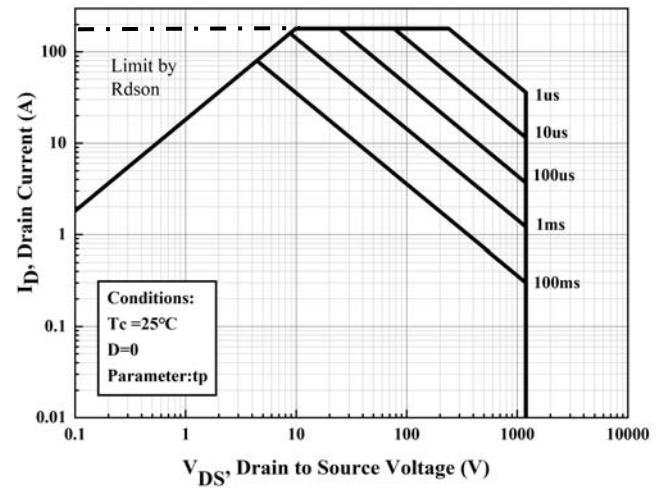


Figure 22. Safe Operating Area

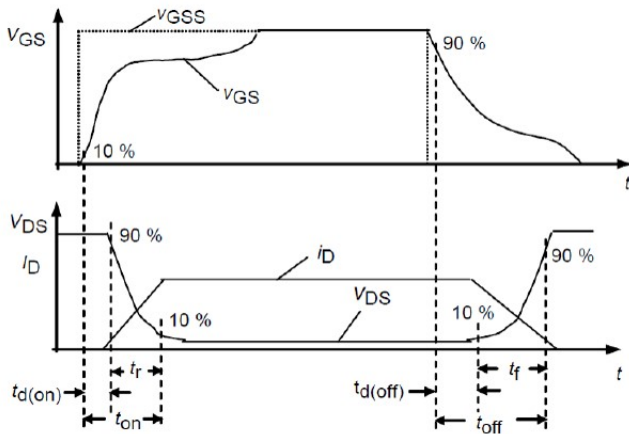


Figure 23. Switching Times Definition

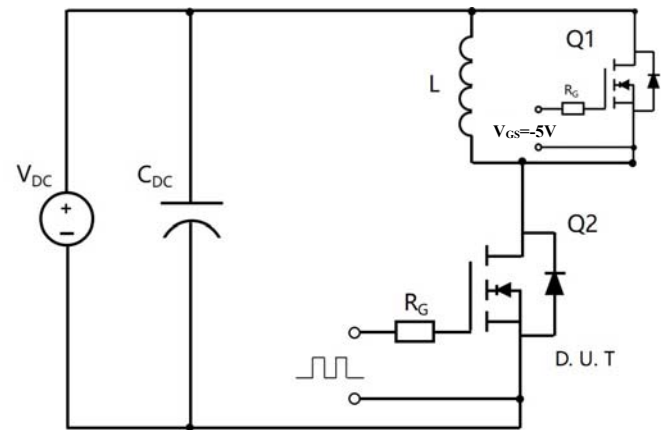
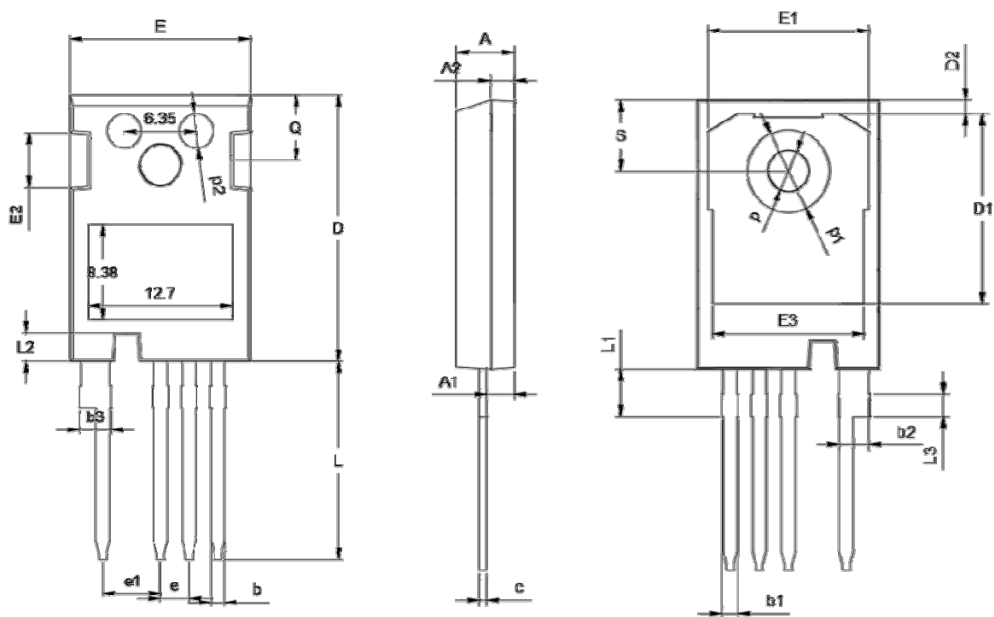


Figure 24. Clamped Inductive Switching Waveform Test Circuit

■Outline Dimensions



TO247-4L			
Dim	Min	Norm	Max
A	4.80	5.00	5.20
A1	2.30	2.40	2.50
A2	1.88	1.98	2.08
b	1.10	1.20	1.30
b1	1.20	/	1.50
b2	2.35	2.55	2.75
b3	2.45	/	2.85
c	0.55	0.60	0.65
D	23.3	23.45	23.6
D1	16.25	16.55	16.85
D2	1.00	/	1.30
e	TYP2.54		
e1	TYP5.06		
E	15.75	15.90	16.05
E1	13.80	/	14.20
E2	4.40	4.75	5.10
E3	13.00	/	13.45
L	17.34	17.49	17.64
L1	4.00	/	4.30
L2	2.35	/	2.65
L3	TYP1.98		
Q	5.60	5.80	6.00
S	6.05	/	6.30
p	TYP3.58		
p1	TYP7.18		
p2	TYP3.00		



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